

FIG. 1

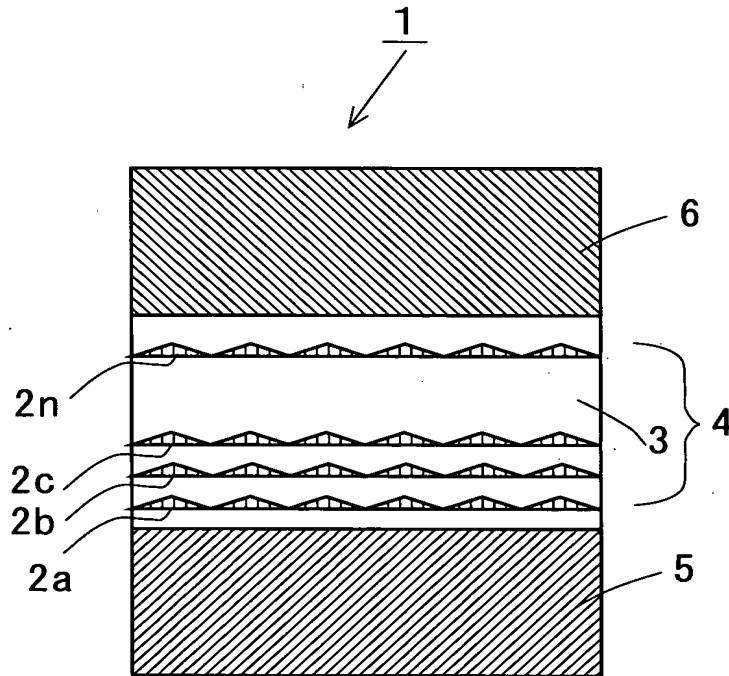


FIG. 2

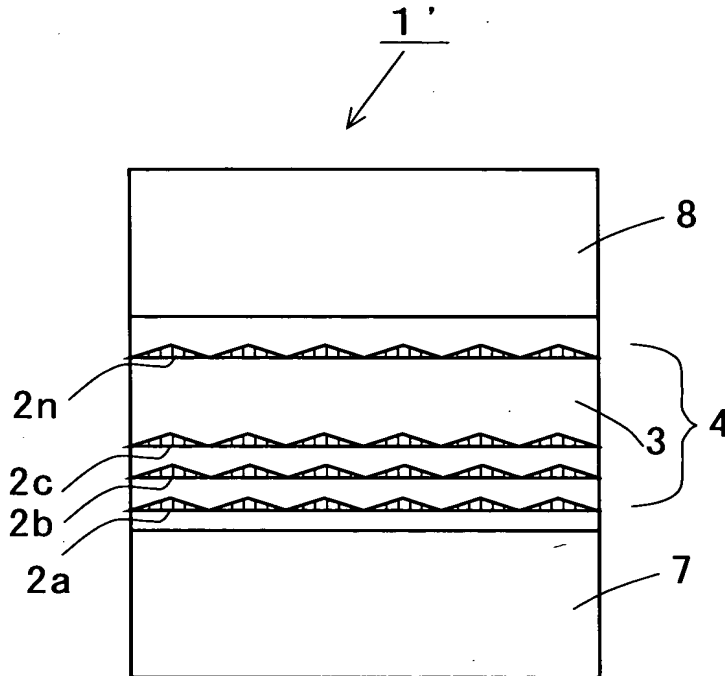


FIG. 3

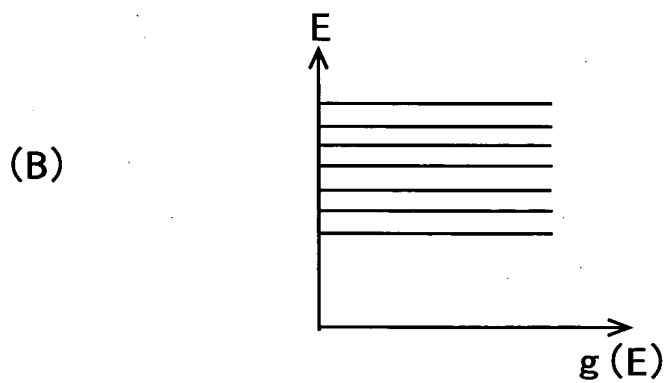
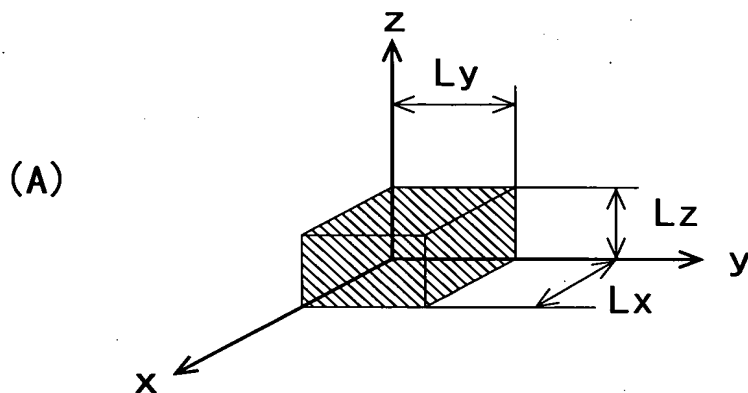


FIG. 4

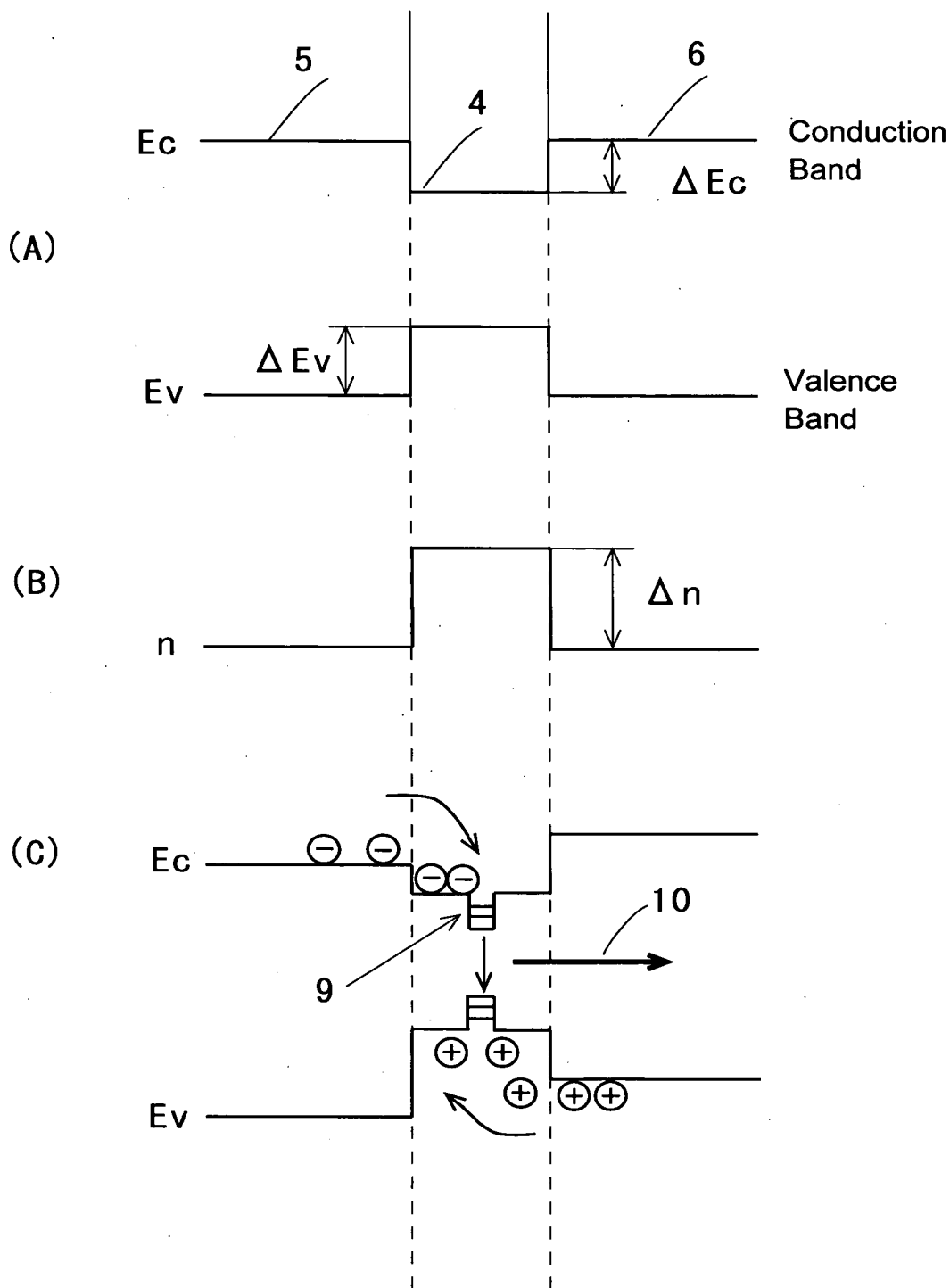


FIG. 5

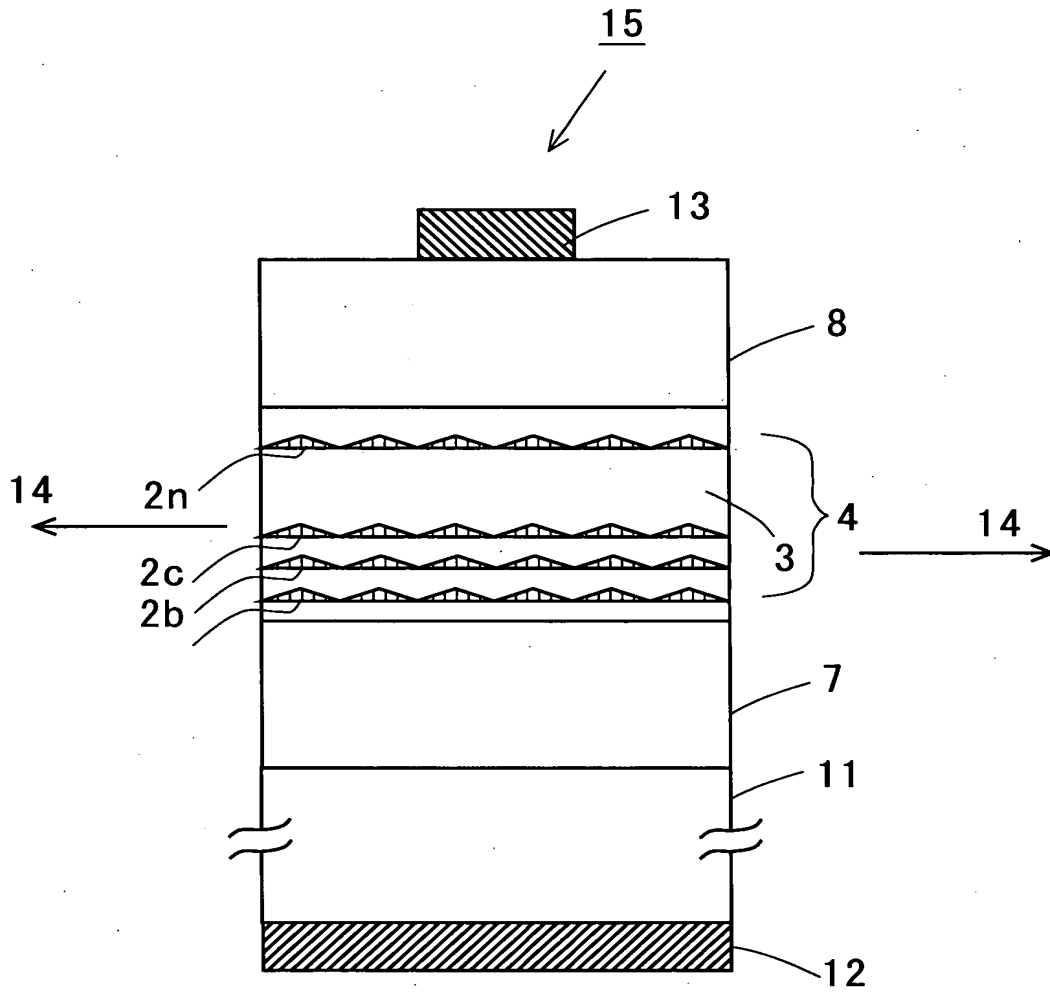


FIG. 6

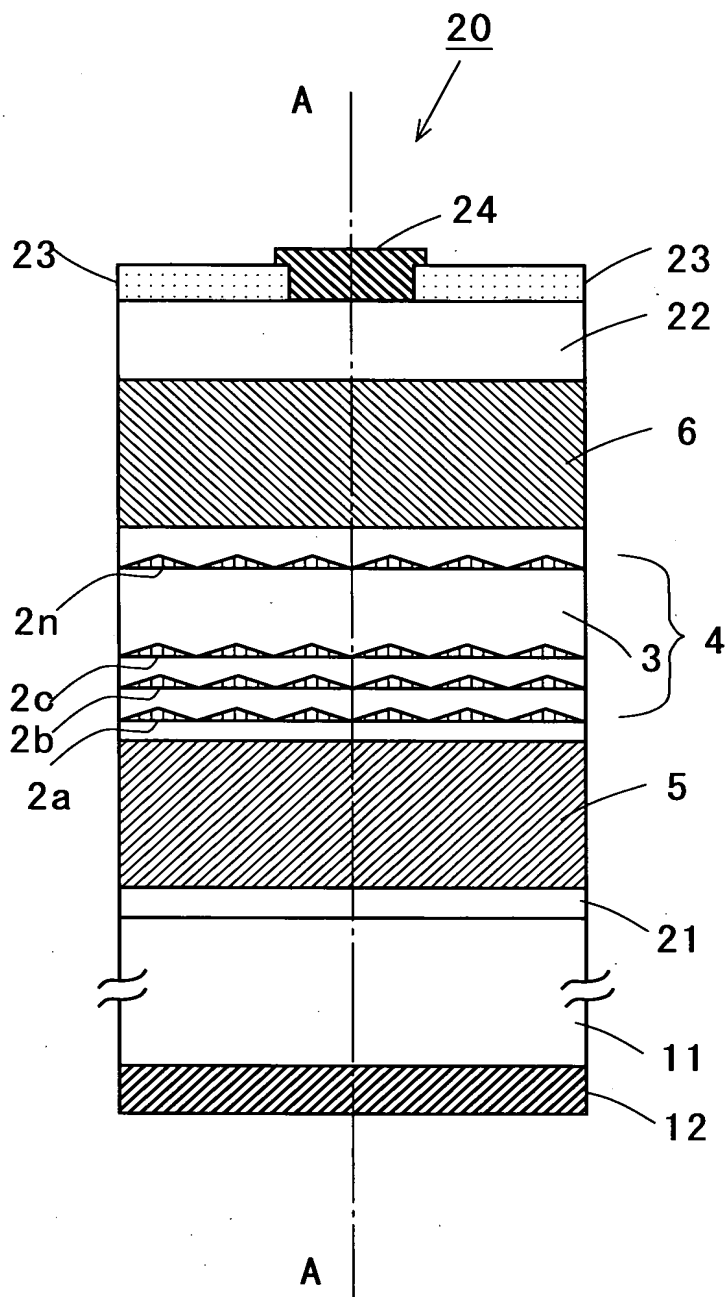
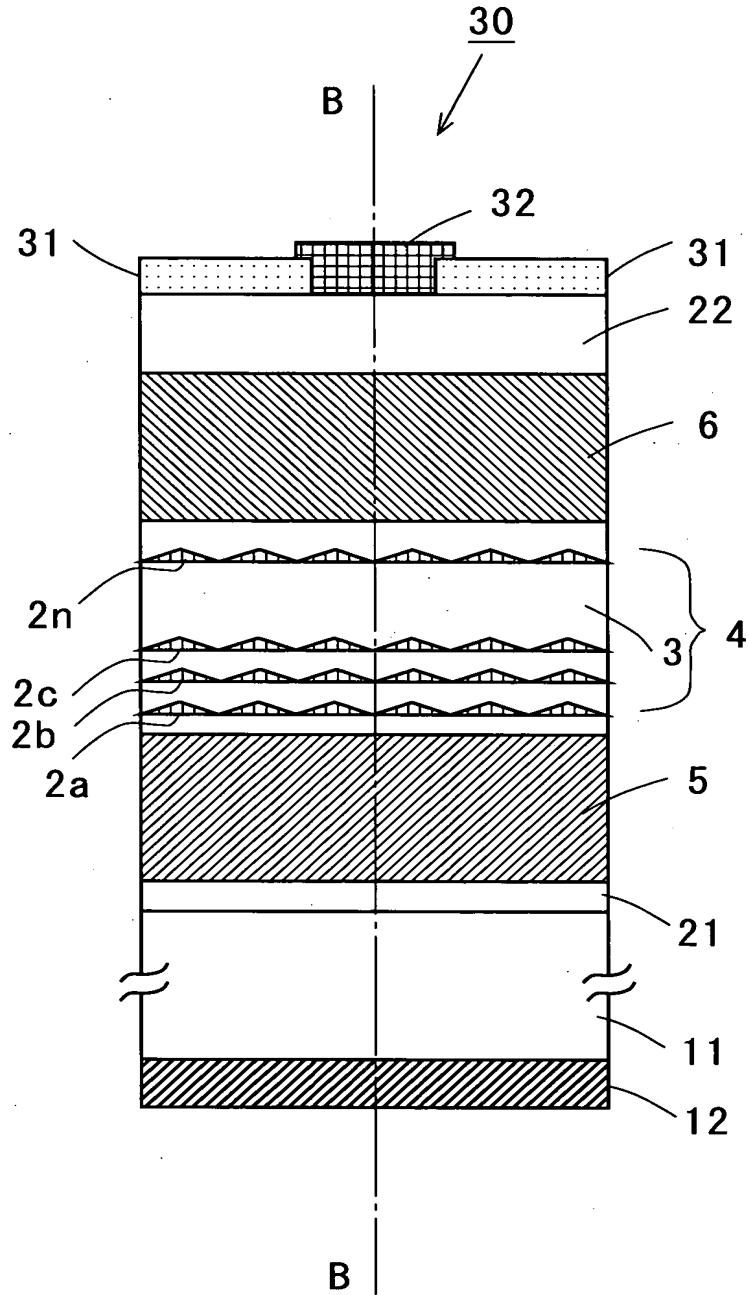


FIG. 8



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FIG. 10

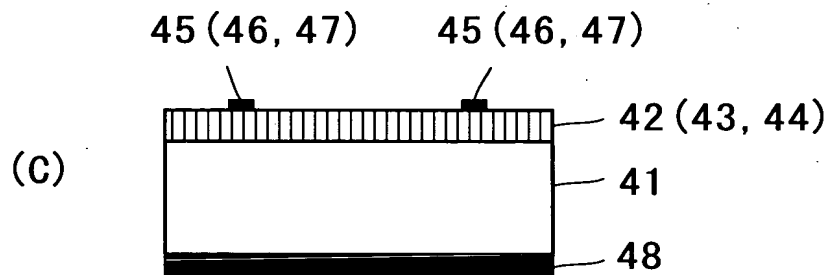
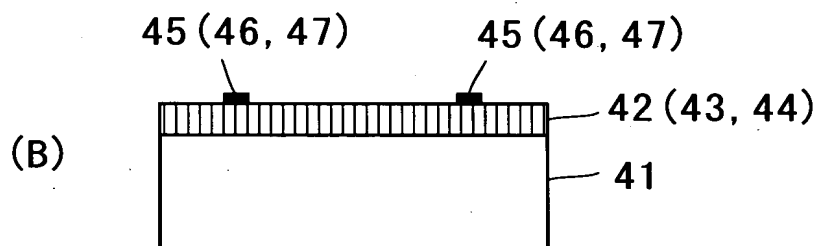
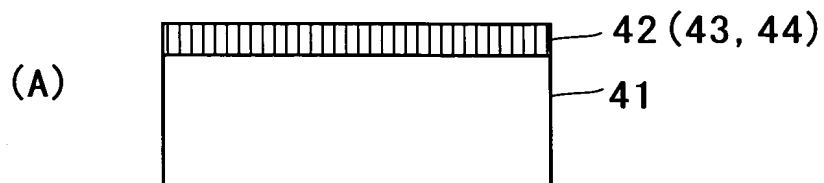


FIG. 11

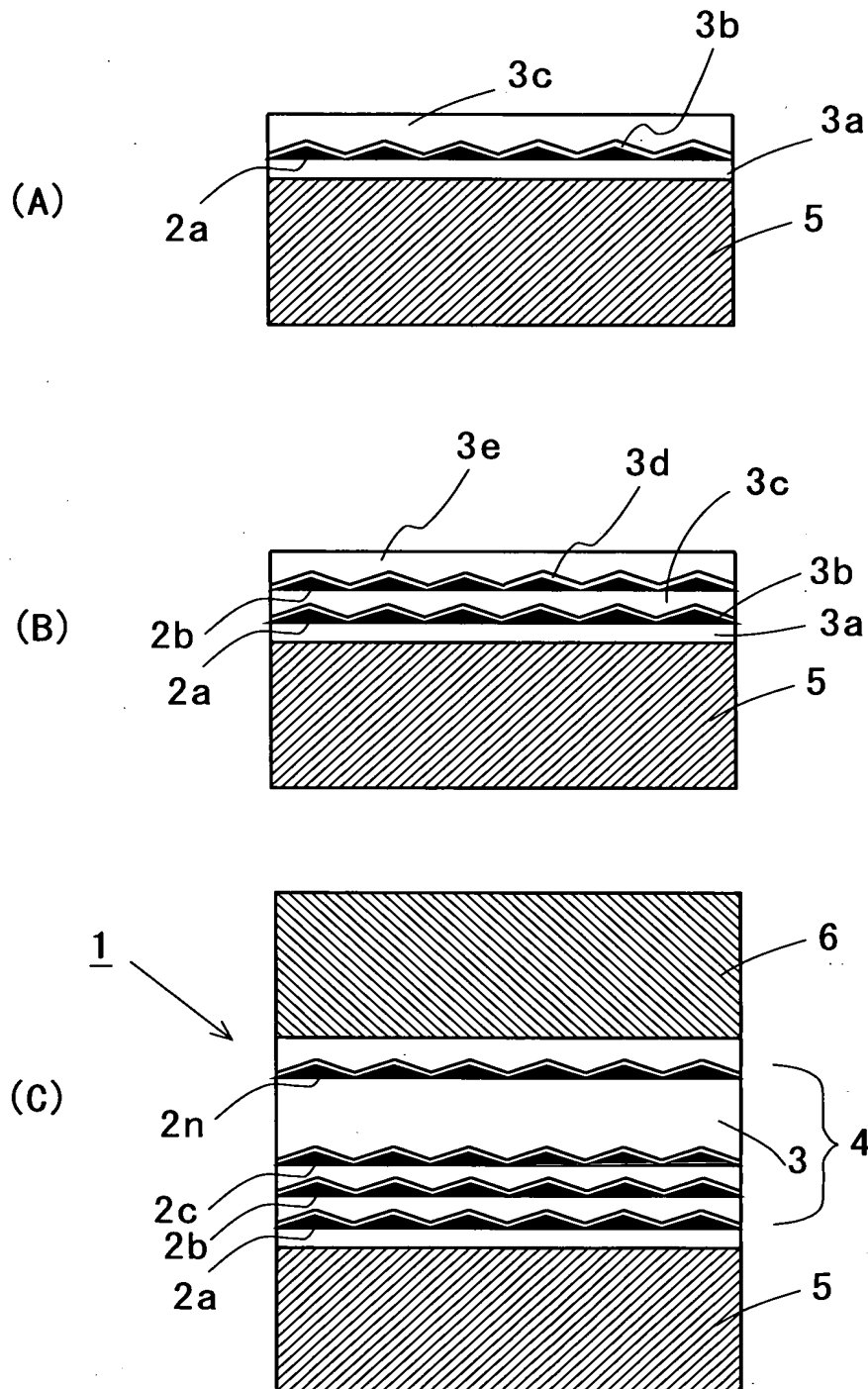


FIG. 12

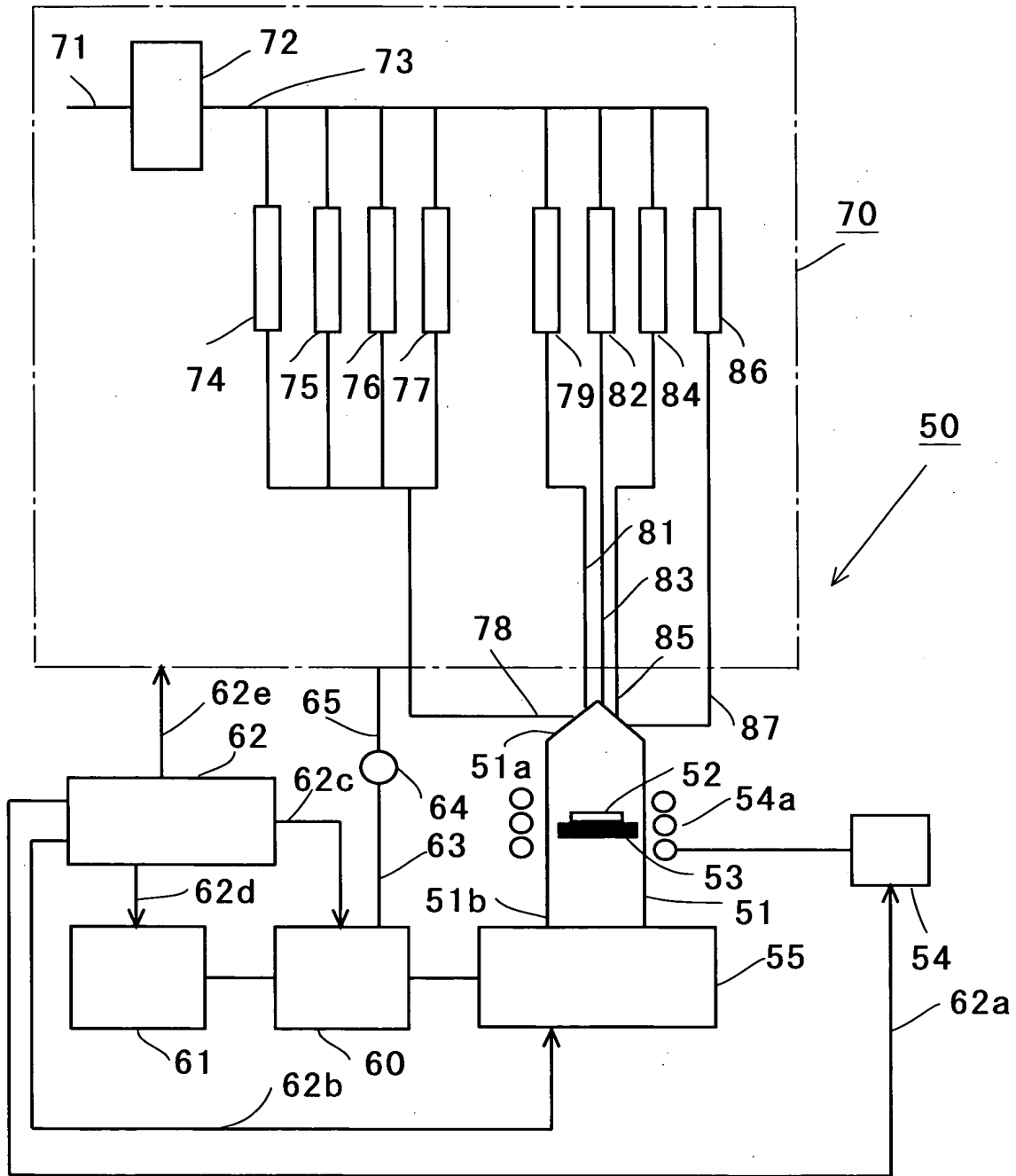


FIG. 13

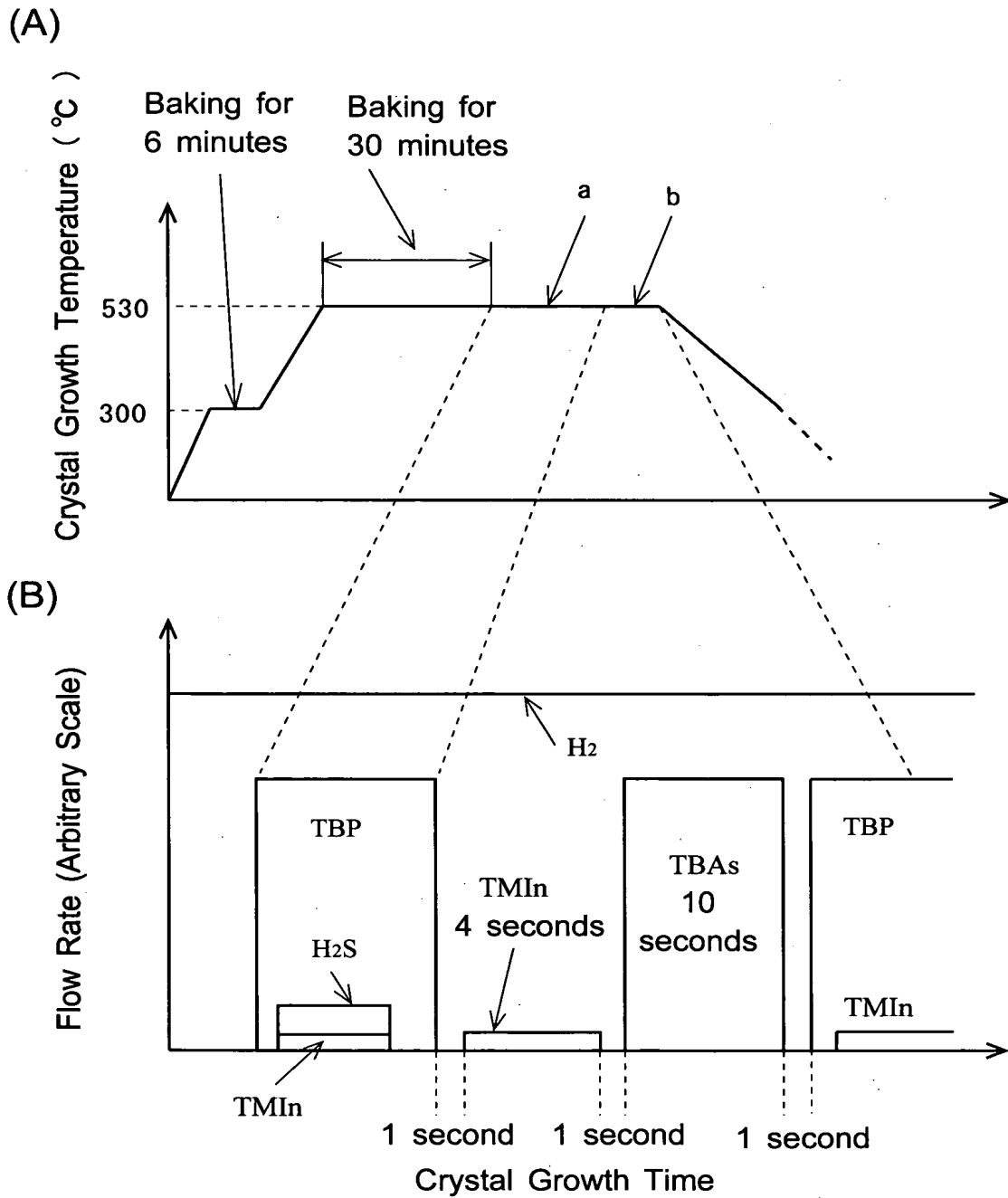
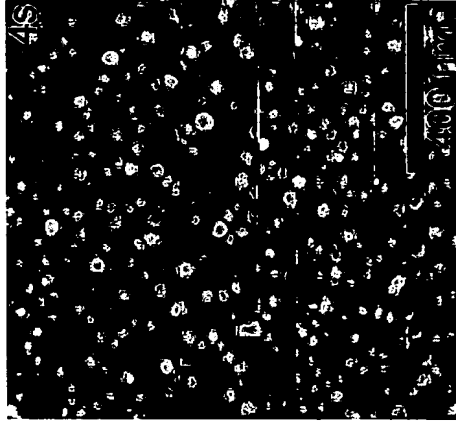
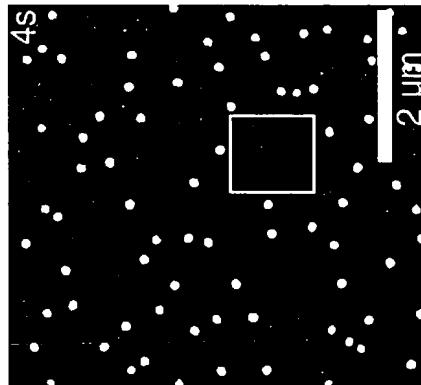


FIG. 14



(B)



(A)

FIG. 15

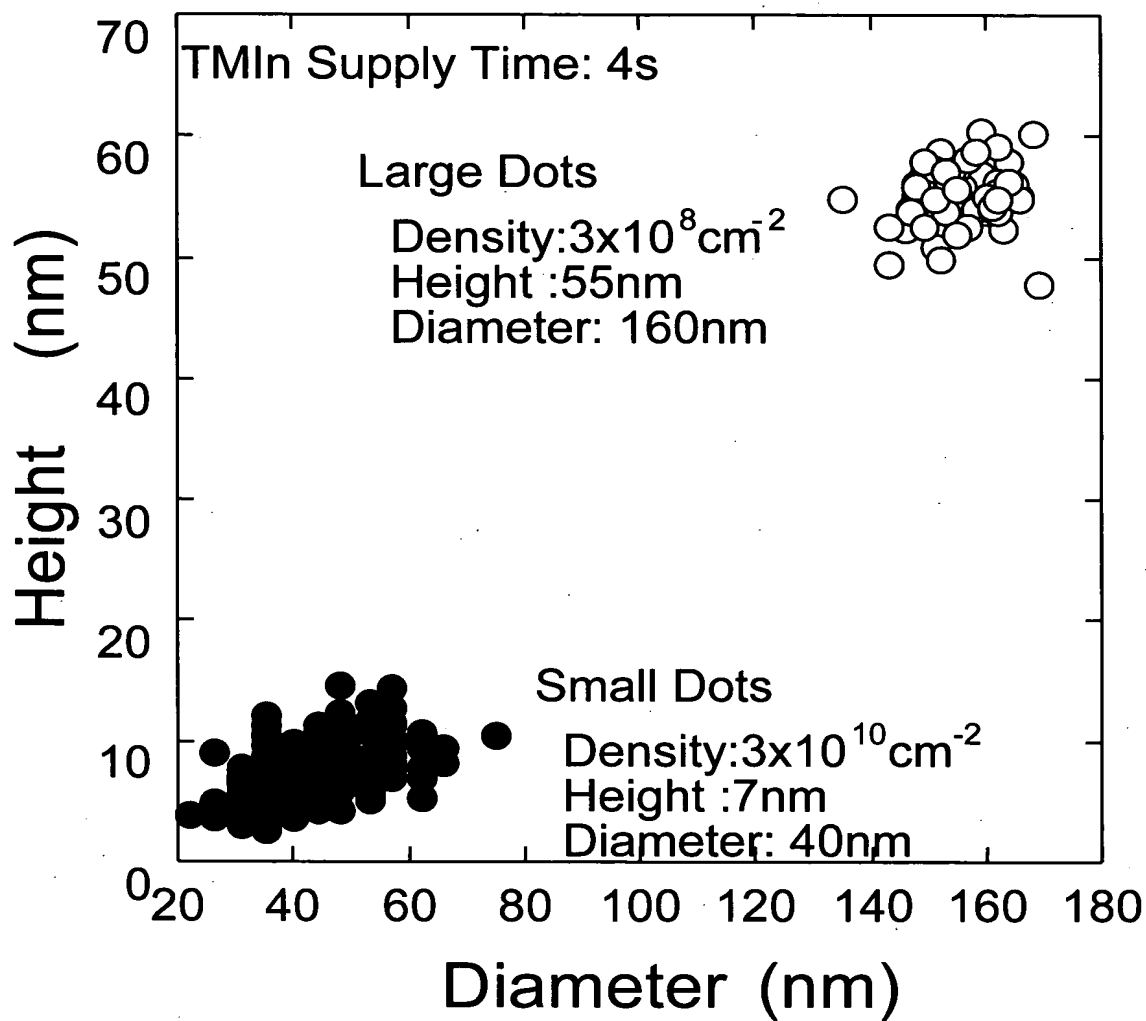


FIG. 16

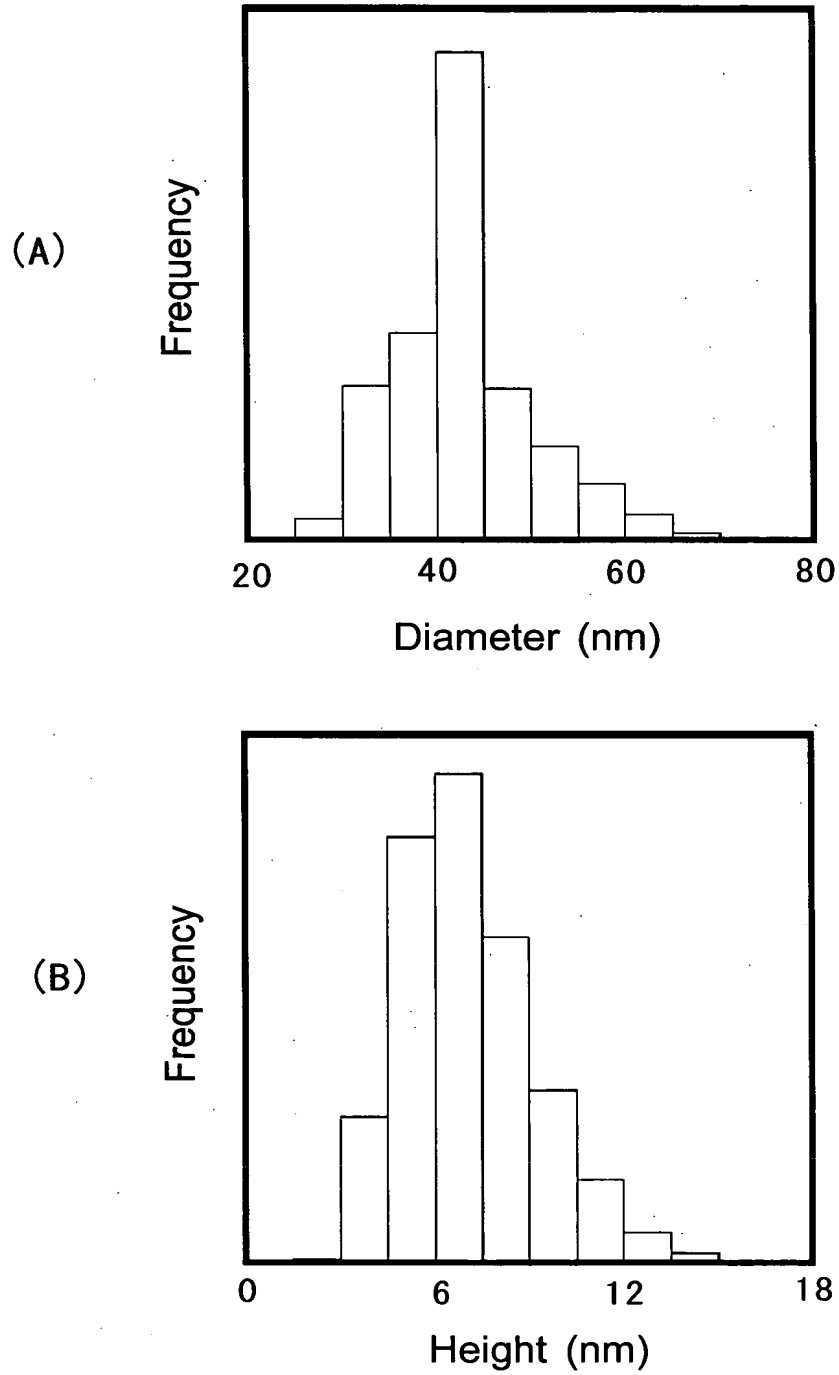


FIG. 17

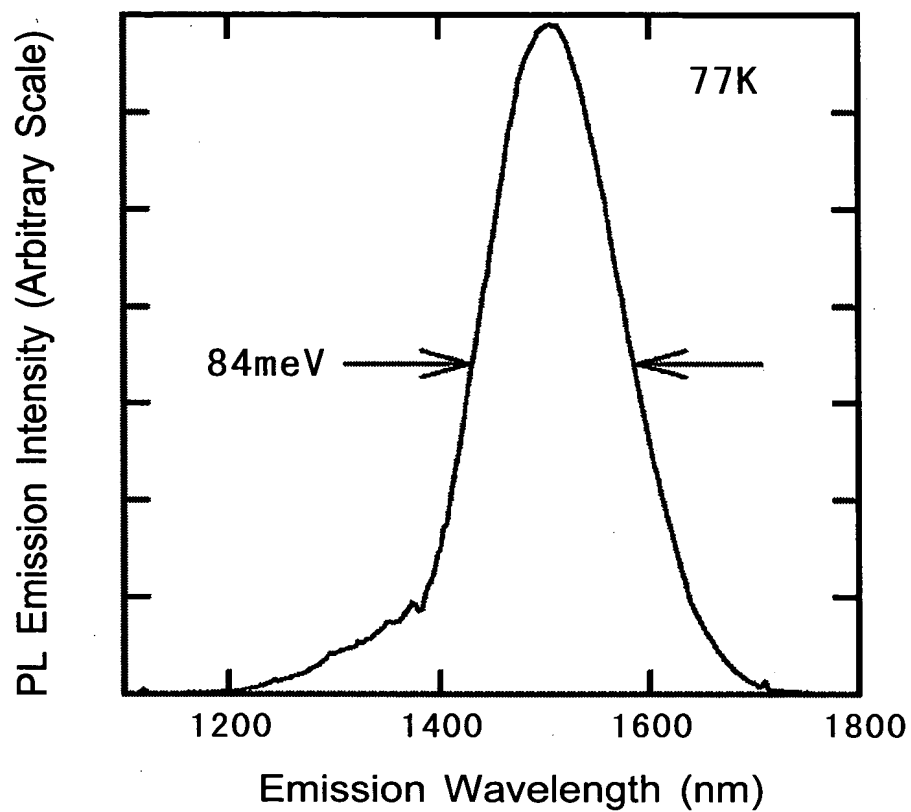


FIG. 18

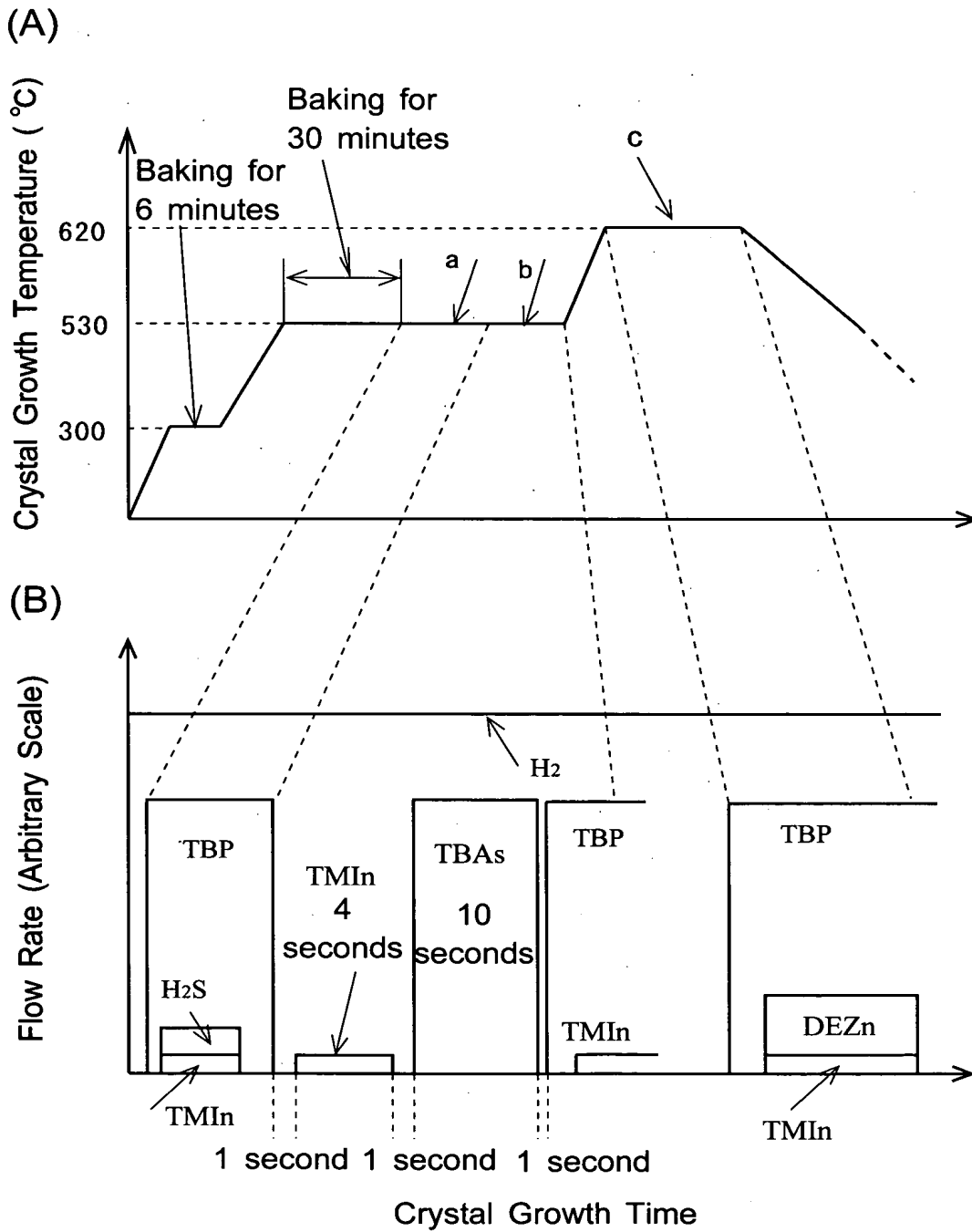


FIG. 19

Gas	Flow Rate (mol/second)
TMIn	1.68×10^{-7}
TBA _s	3.38×10^{-6}
TBP	3.38×10^{-6}
DEZn	9.05×10^{-8}

FIG. 20

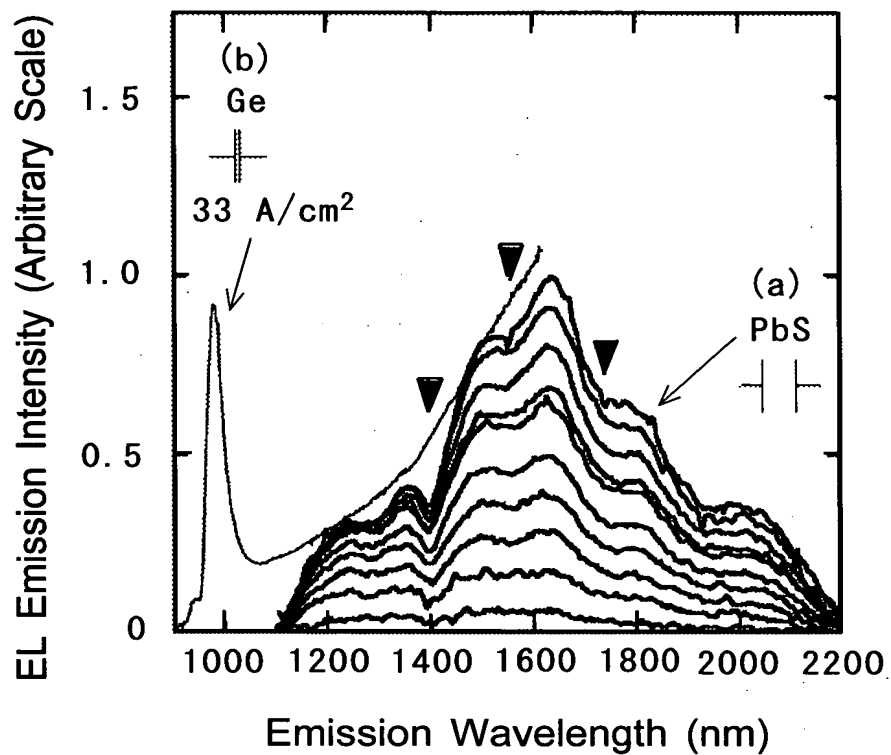


FIG. 21

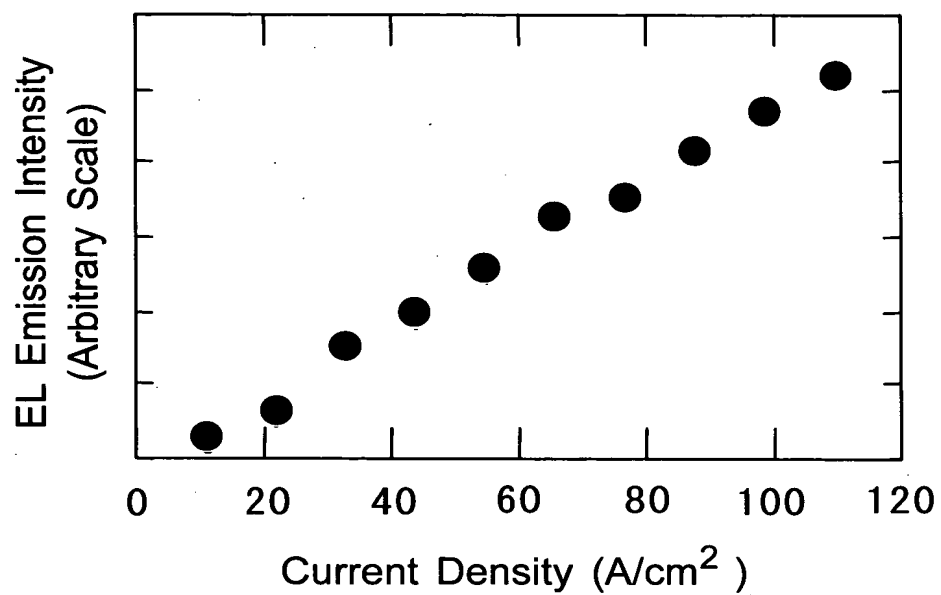


FIG. 22

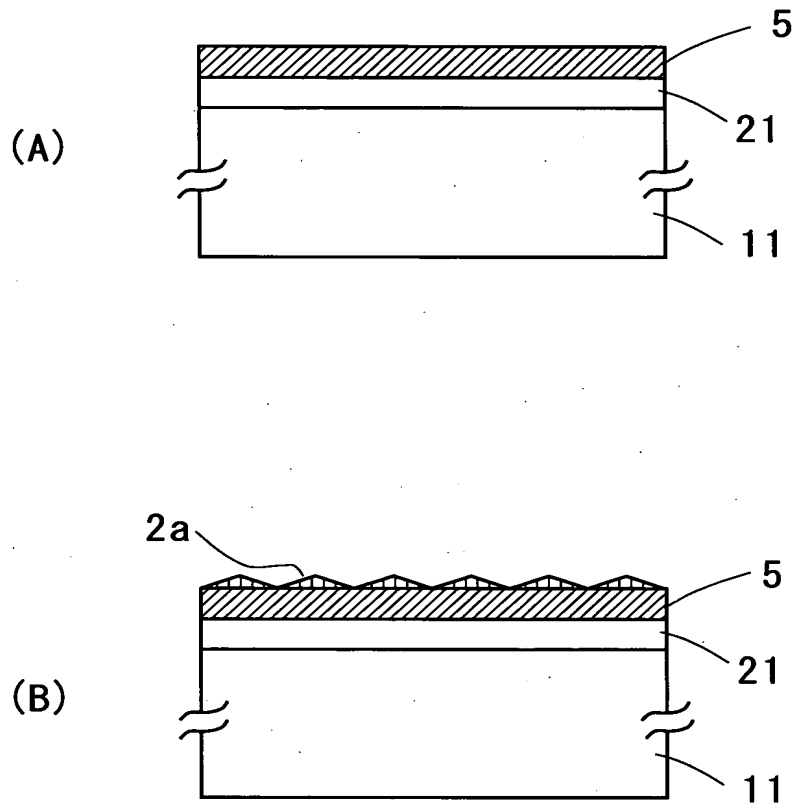


FIG. 23

Growth Apparatus	MOCVD
Growth Temperature	530°C
Pressure	7.6 Torr
Carrier Gas	H ₂ 4 s.l.m
TMI n Flow Rate	1.01×10^{-5} mol/minute
TMI n Supply time	0 ~ 8 seconds
TBA s Flow Rate	2.01×10^{-4} mol/minute
Substrate	InP (100)

FIG. 24

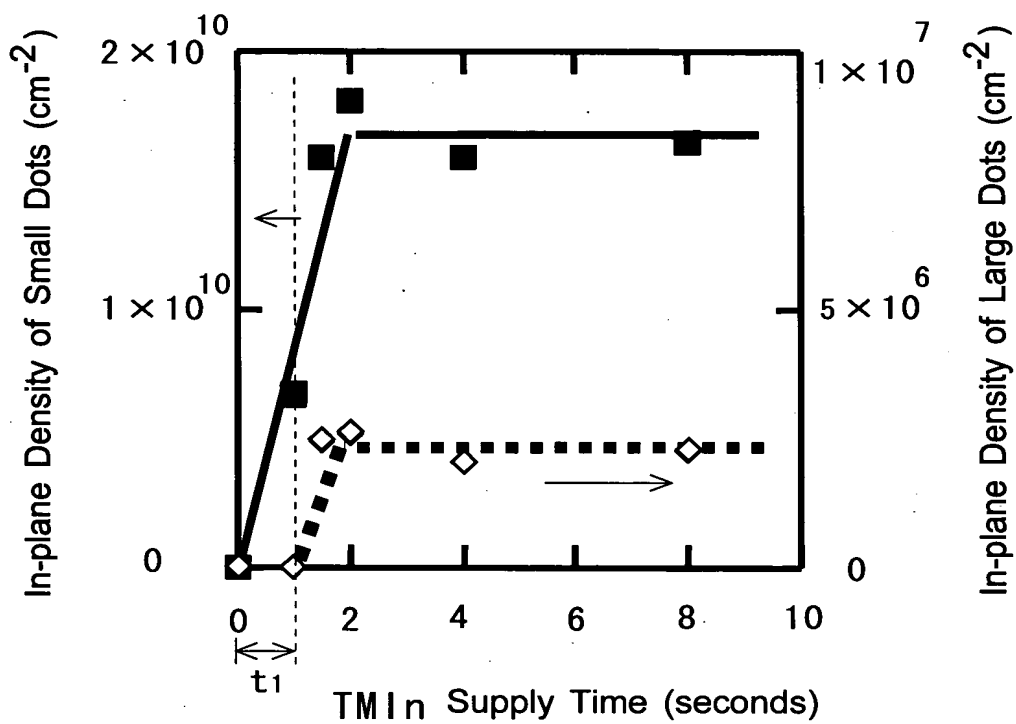


FIG. 25

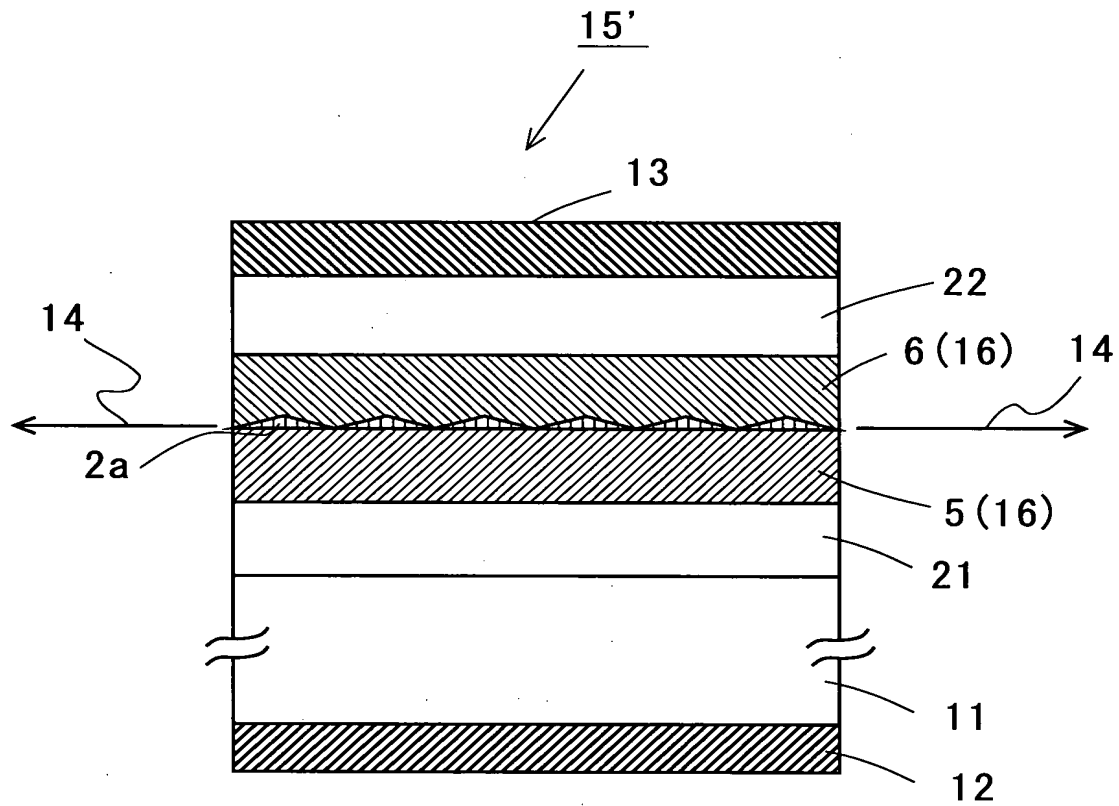


FIG. 26

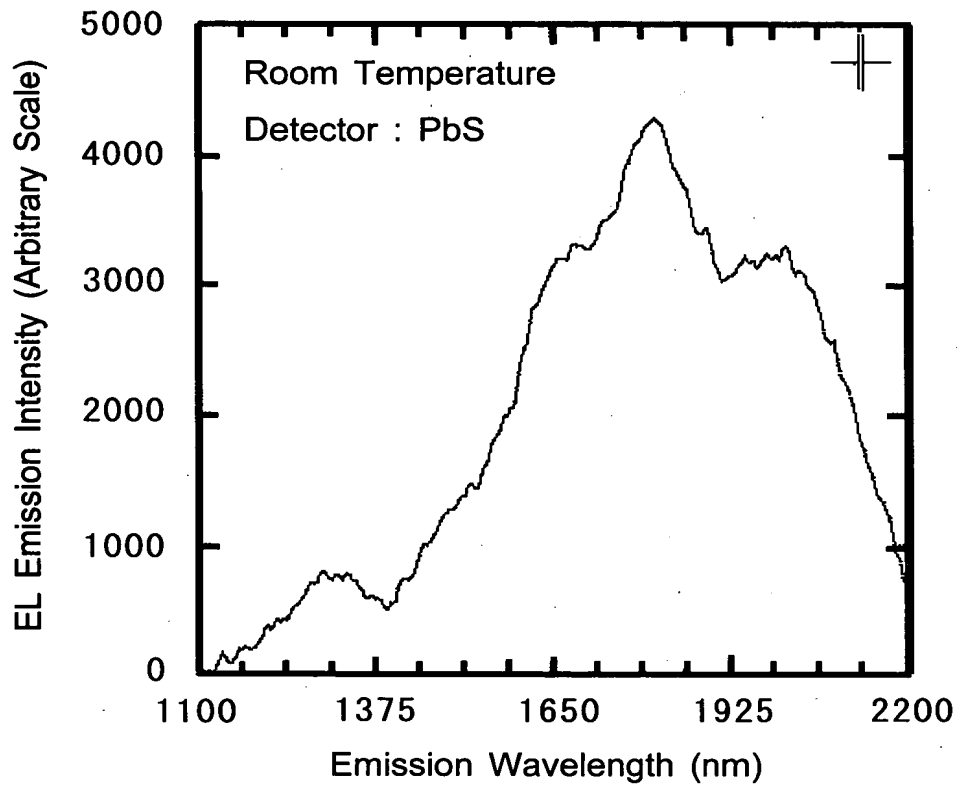


FIG. 27

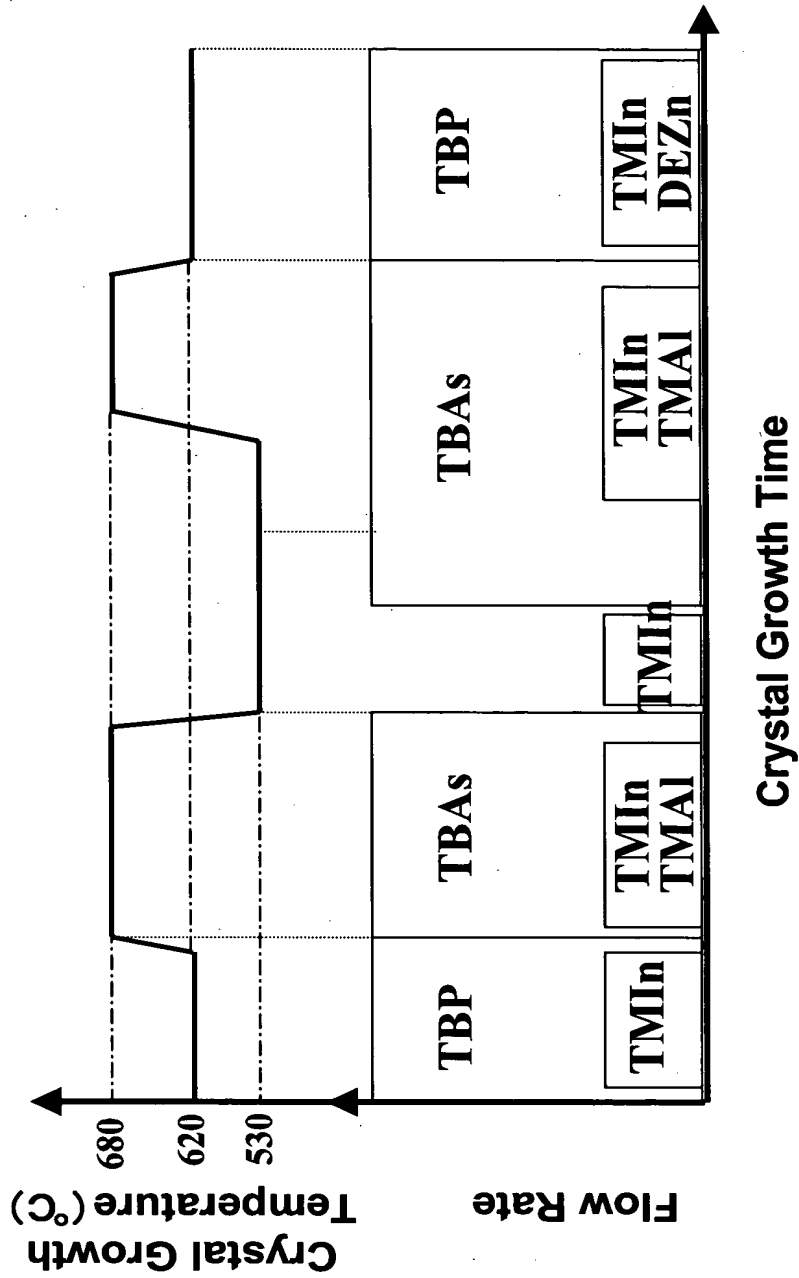


FIG. 28

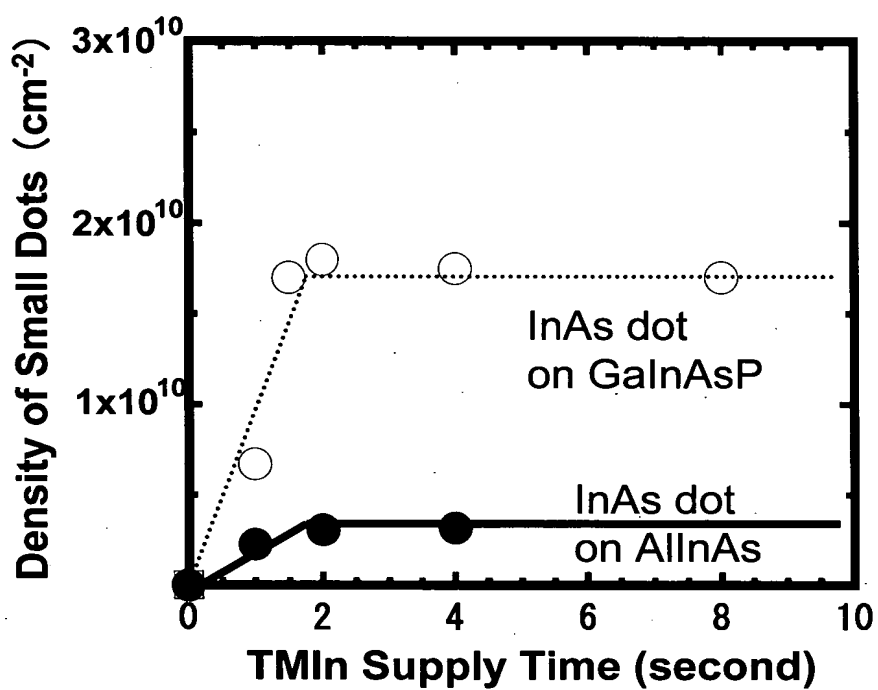
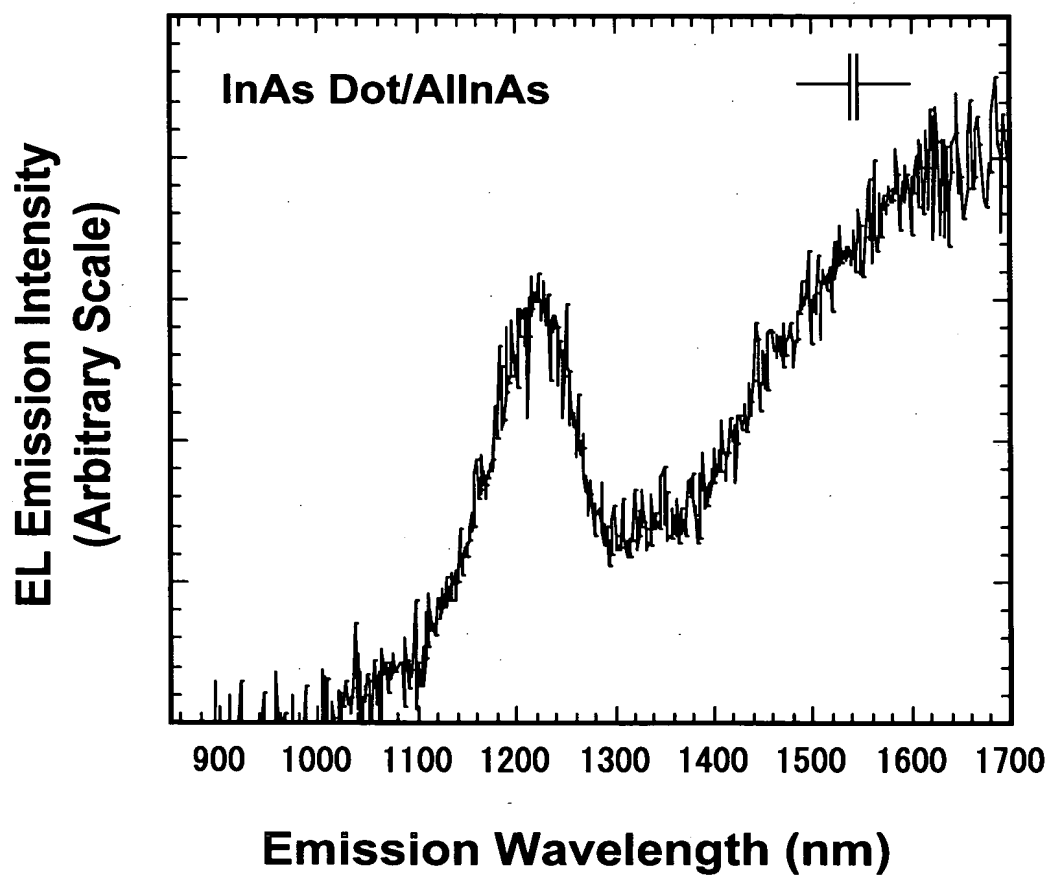


FIG. 29



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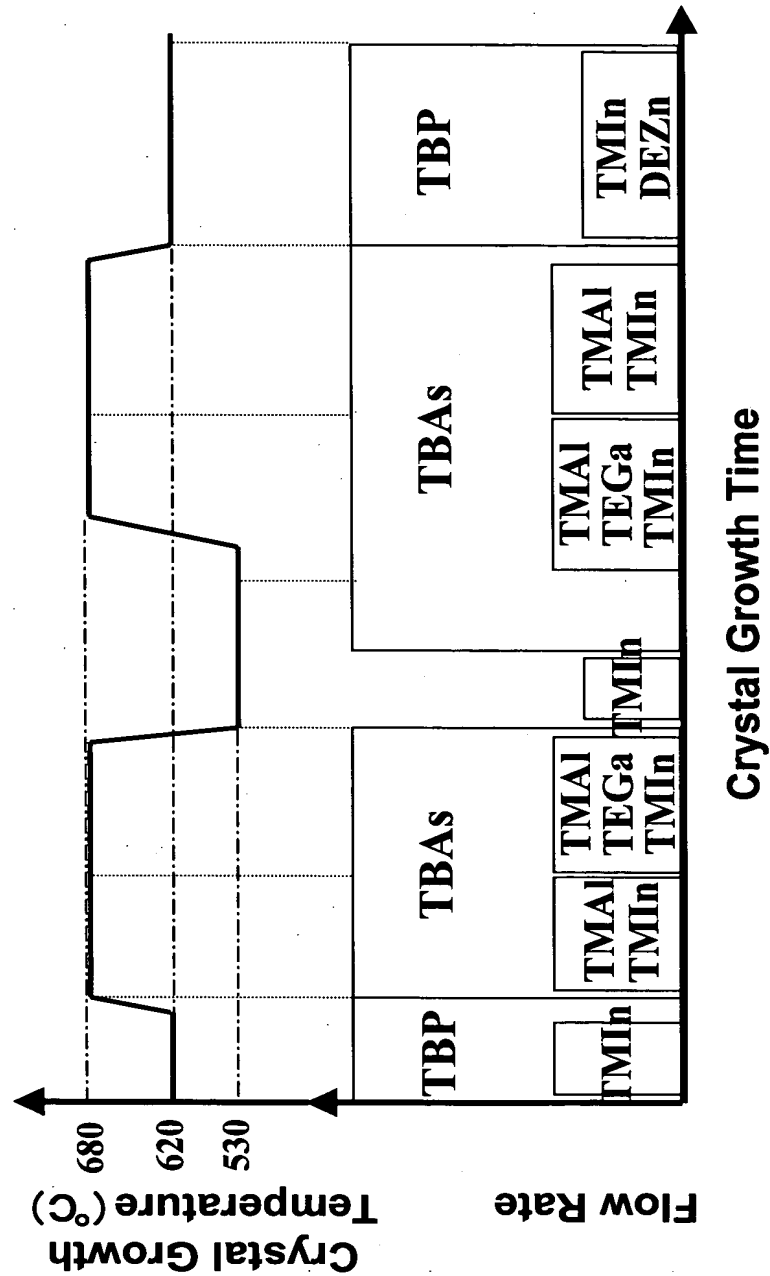


FIG. 31

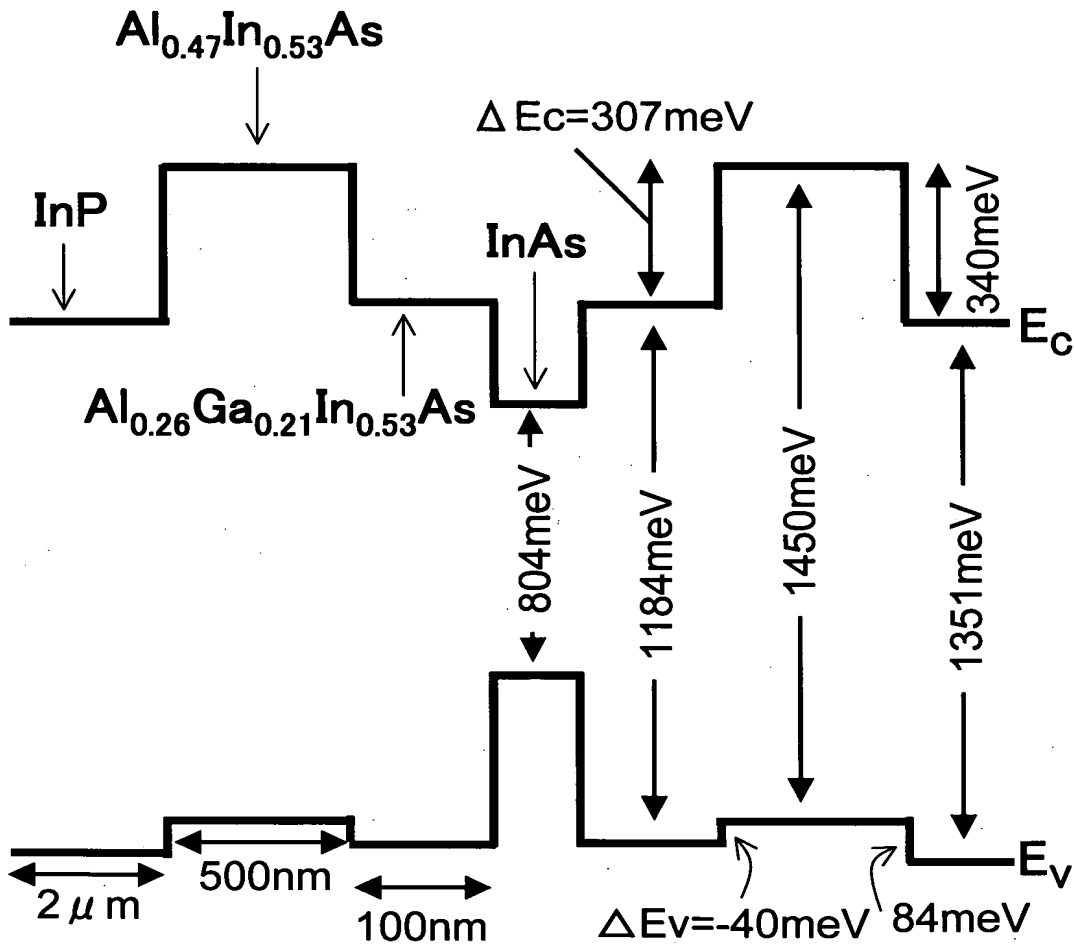


FIG. 32

